

MITSUBISHI IGBT MODULES

# CM200TU-12F

HIGH POWER SWITCHING USE

## CM200TU-12F



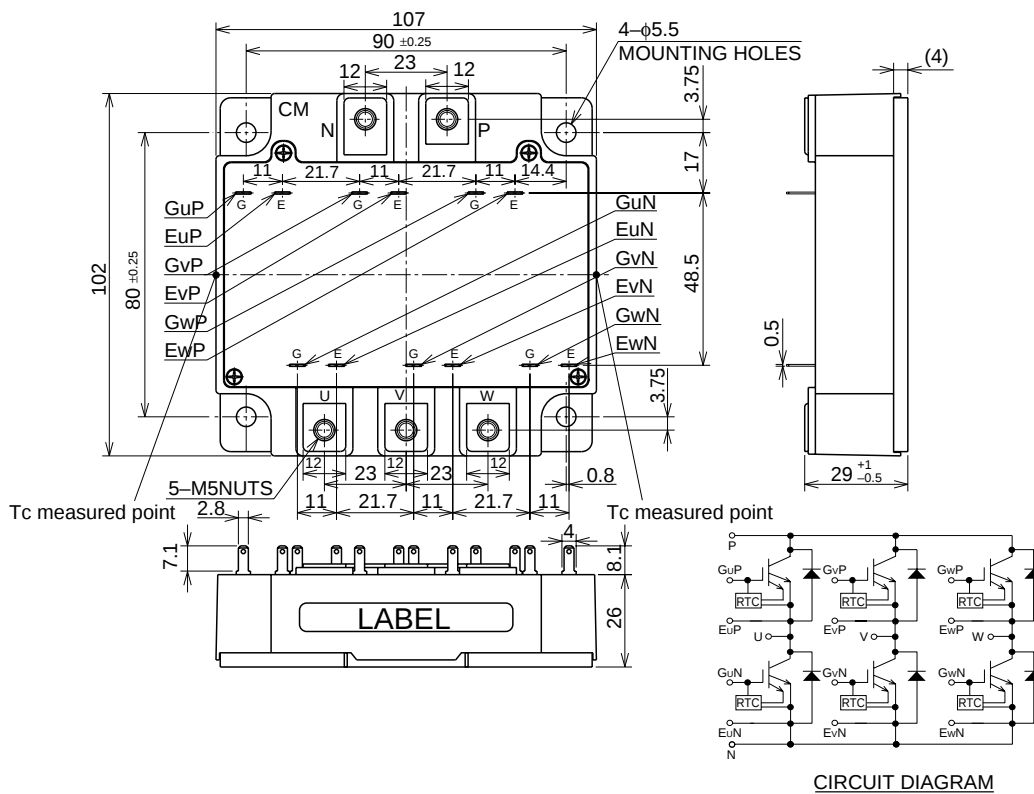
- Ic ..... 200A
- VCES ..... 600V
- Insulated Type
- 6-elements in a pack

## APPLICATION

General purpose inverters & Servo controls, etc

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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### MAXIMUM RATINGS (Tj = 25°C)

| Symbol                   | Parameter                     | Conditions                             | Ratings    | Unit  |
|--------------------------|-------------------------------|----------------------------------------|------------|-------|
| V <sub>CES</sub>         | Collector-emitter voltage     | G-E Short                              | 600        | V     |
| V <sub>GES</sub>         | Gate-emitter voltage          | C-E Short                              | ±20        | V     |
| I <sub>C</sub>           | Collector current             | T <sub>C</sub> = 25°C                  | 200        | A     |
| I <sub>CM</sub>          |                               | Pulse (Note 2)                         | 400        |       |
| I <sub>E</sub> (Note 1)  | Emitter current               | T <sub>C</sub> = 25°C                  | 200        | A     |
| I <sub>EM</sub> (Note 1) |                               | Pulse (Note 2)                         | 400        |       |
| P <sub>C</sub> (Note 3)  | Maximum collector dissipation | T <sub>C</sub> = 25°C                  | 590        | W     |
| T <sub>j</sub>           | Junction temperature          |                                        | −40 ~ +150 | °C    |
| T <sub>stg</sub>         | Storage temperature           |                                        | −40 ~ +125 | °C    |
| V <sub>iso</sub>         | Isolation voltage             | Main terminal to base plate, AC 1 min. | 2500       | V     |
| —                        | Torque strength               | Main Terminal M5                       | 2.5 ~ 3.5  | N • m |
| —                        |                               | Mounting holes M5                      | 2.5 ~ 3.5  | N • m |
| —                        | Weight                        | Typical value                          | 680        | g     |

### ELECTRICAL CHARACTERISTICS (Tj = 25°C)

| Symbol                   | Parameter                            | Test conditions                                                                                                                                                                  | Limits |      |        | Unit |
|--------------------------|--------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|------|--------|------|
|                          |                                      |                                                                                                                                                                                  | Min.   | Typ. | Max.   |      |
| I <sub>CES</sub>         | Collector cutoff current             | V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V                                                                                                                        | —      | —    | 1      | mA   |
| V <sub>GE(th)</sub>      | Gate-emitter threshold voltage       | I <sub>C</sub> = 20mA, V <sub>CE</sub> = 10V                                                                                                                                     | 5      | 6    | 7      | V    |
| I <sub>GES</sub>         | Gate leakage current                 | V <sub>GE</sub> = V <sub>CES</sub> , V <sub>CE</sub> = 0V                                                                                                                        | —      | —    | 20     | μA   |
| V <sub>CE(sat)</sub>     | Collector-emitter saturation voltage | T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 125°C                                                                                                                                  | —      | 1.6  | 2.2    | V    |
| C <sub>ies</sub>         | Input capacitance                    | V <sub>CE</sub> = 10V<br>V <sub>GE</sub> = 0V                                                                                                                                    | —      | —    | 54     |      |
| C <sub>oes</sub>         | Output capacitance                   |                                                                                                                                                                                  | —      | —    | 3.6    | nF   |
| C <sub>res</sub>         | Reverse transfer capacitance         |                                                                                                                                                                                  | —      | —    | 2.0    |      |
| Q <sub>G</sub>           | Total gate charge                    | V <sub>CC</sub> = 300V, I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V                                                                                                             | —      | 1240 | —      | nC   |
| t <sub>d(on)</sub>       | Turn-on delay time                   | V <sub>CC</sub> = 300V, I <sub>C</sub> = 200A<br>V <sub>GE1</sub> = V <sub>GE2</sub> = 15V<br>R <sub>G</sub> = 3.1Ω, Inductive load switching operation<br>I <sub>E</sub> = 200A | —      | —    | 120    | ns   |
| t <sub>r</sub>           | Turn-on rise time                    |                                                                                                                                                                                  | —      | —    | 100    |      |
| t <sub>d(off)</sub>      | Turn-off delay time                  |                                                                                                                                                                                  | —      | —    | 350    |      |
| t <sub>f</sub>           | Turn-off fall time                   |                                                                                                                                                                                  | —      | —    | 250    |      |
| t <sub>rr</sub> (Note 1) | Reverse recovery time                |                                                                                                                                                                                  | —      | —    | 150    | ns   |
| Q <sub>rr</sub> (Note 1) | Reverse recovery charge              |                                                                                                                                                                                  | —      | 3.8  | —      | μC   |
| V <sub>EC</sub> (Note 1) | Emitter-collector voltage            | I <sub>E</sub> = 200A, V <sub>GE</sub> = 0V                                                                                                                                      | —      | —    | 2.6    | V    |
| R <sub>th(j-c)Q</sub>    | Thermal resistance*1                 | IGBT part (1/6 module)                                                                                                                                                           | —      | —    | 0.21   | °C/W |
| R <sub>th(j-c)R</sub>    |                                      | FWDi part (1/6 module)                                                                                                                                                           | —      | —    | 0.35   |      |
| R <sub>th(c-f)</sub>     | Contact thermal resistance           | Case to fin, Thermal compound applied*2 (1/6 module)                                                                                                                             | —      | 0.09 | —      |      |
| R <sub>th(j-c')Q</sub>   | Thermal resistance                   | T <sub>C</sub> measured point is just under the chips                                                                                                                            | —      | —    | 0.15*3 |      |
| R <sub>G</sub>           | External gate resistance             |                                                                                                                                                                                  | 3.1    | —    | 31     | Ω    |

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub>, Q<sub>rr</sub>, die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode. (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

\*1 : T<sub>C</sub> measured point is indicated in OUTLINE DRAWING.

\*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

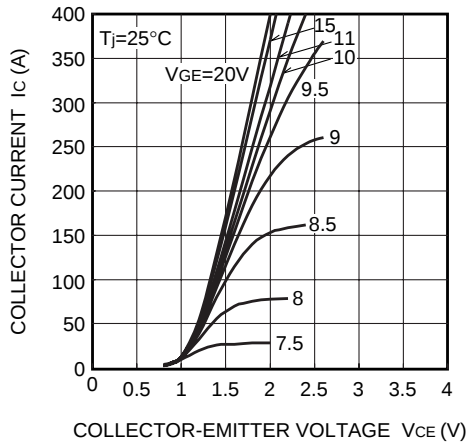
\*3 : If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

# CM200TU-12F

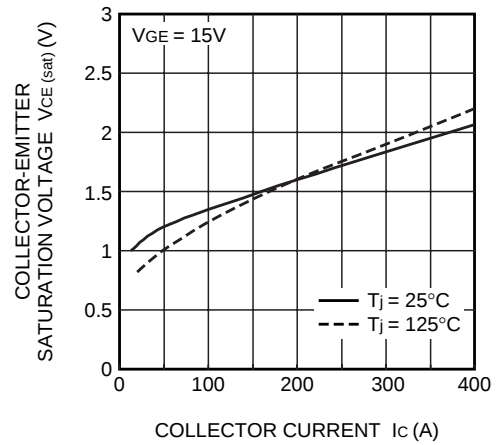
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

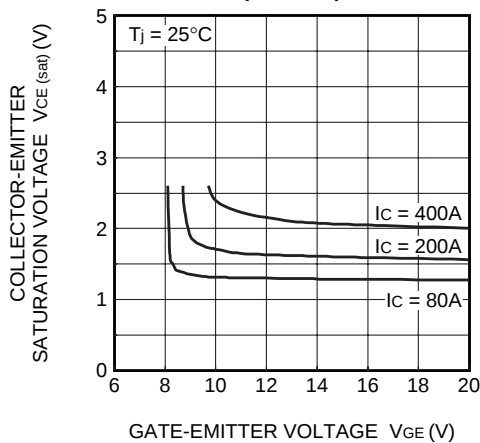
OUTPUT CHARACTERISTICS  
(TYPICAL)



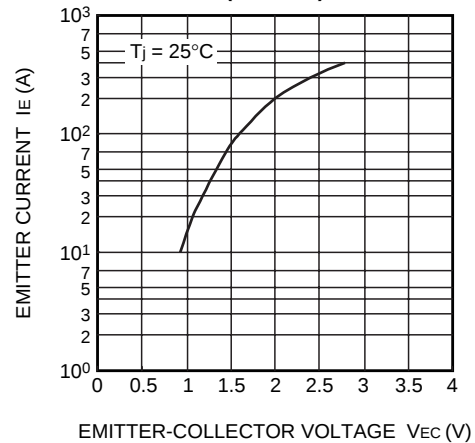
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



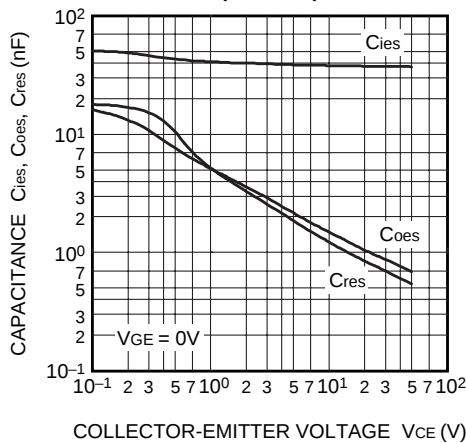
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



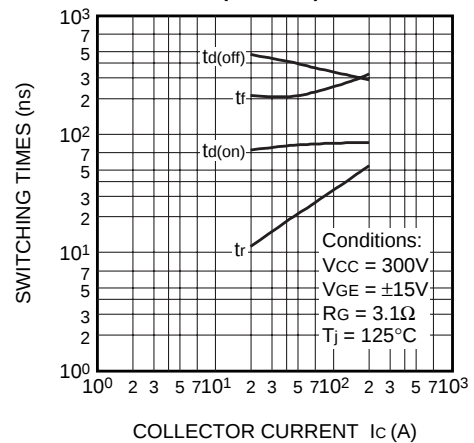
FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



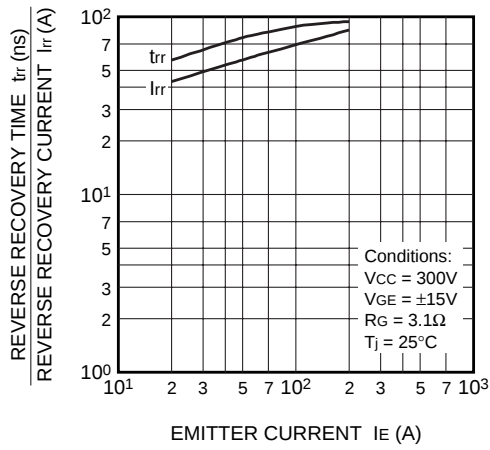
CAPACITANCE- $V_{ce}$   
CHARACTERISTICS  
(TYPICAL)



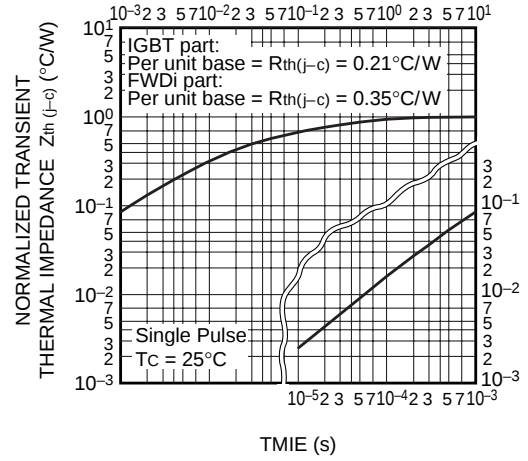
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE  
(TYPICAL)



TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(IGBT part & FWDi part)



GATE CHARGE  
CHARACTERISTICS  
(TYPICAL)

